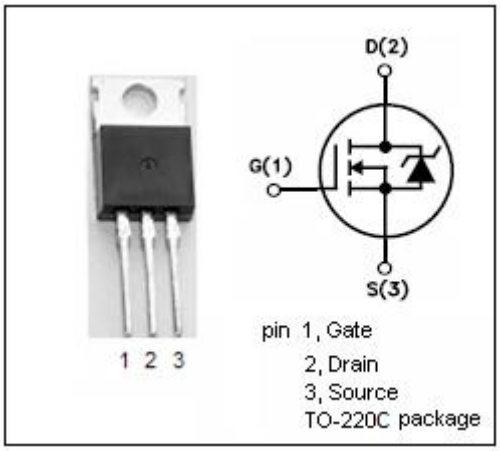
isc N-Channel MOSFET Transistor FQP20N06L

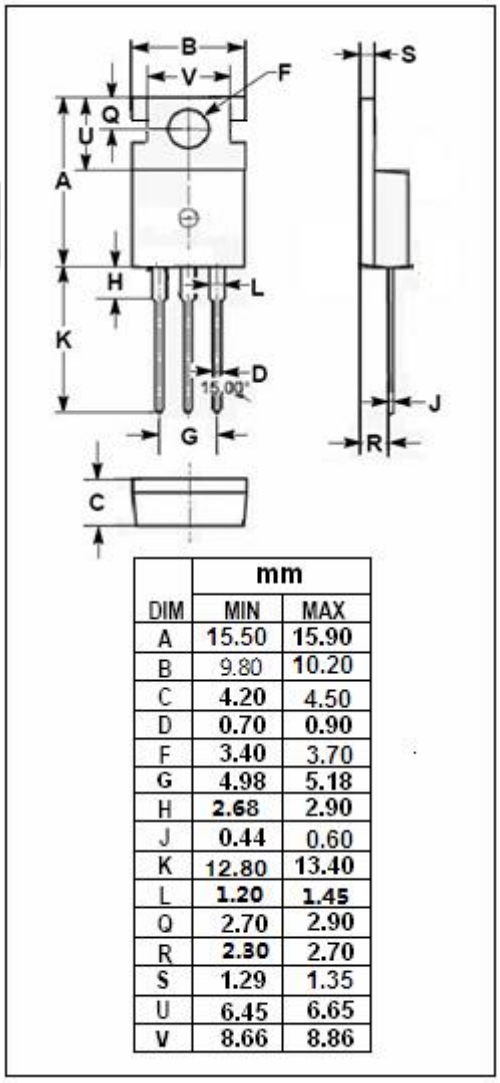


DESCRIPTION

- Drain Current I_D=21A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=60V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 55mΩ (Max)
- 100% Avalanche Tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- High current , high speed switching
- Switch mode power supplies



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current-continuous@ T_C=25℃	21	A
I_{DM}	Pulse Drain Current	84	A
P_D	Power Dissipation @TC=25℃	60	W
T_j	Max. Operating Junction Temperature	-55~175	℃
T_{stg}	Storage Temperature Range	-55~175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to case	2.5	℃/W

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 250uA	60			V
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= 250uA	1	1.6	2.5	V
$R_{DS(ON)}$	Drain-Source On-stage Resistance	V_{GS}= 10V; I_D= 10A		35	55	mΩ
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±20V; V_{DS}= 0			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 60V; V_{GS}= 0			1	uA
V_{SD}	Diode Forward Voltage	I_S= 21A; V_{GS}= 0			1.5	V

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